

Process		38 um Thick Photoresist Process
		AZ 9260
Dehydration Bake (hot plate)	temp (°C)	200
	time (min)	5
HMDS (dynamic) spin	speed (rpm)	2000
	time (s)	30
Spin coating AZ9260	speed (rpm)	300
	time (s)	3
	speed (rpm)	900
	acceleration (rpm/s)	1500
	time (s)	80
Wait	time (s)	60
Soft-bake (hotplate)	temp (°C)	90
	time (min)	1
	temp (°C)	110
	time (min)	4
If double coating, repeat spin coating step above		
Wait	time (s)	60
Soft-bake (hotplate)	temp (°C)	90
	time (min)	1
	temp (°C)	110
	time (min)	8
Wait	time (s)	60
Expose (12mW/cm <sup>2</sup> )	mode	SC (multiple exposure 3 cycles 30 sec each w/ 10 sec gap)
	time (s)	90
Develop	developer	AZ 400K
	developer: di water ratio	1:4

1. Use a minimum of 100 ml of AZ 400K developer for a 4-inch wafer to avoid the slow-down of the development rate due to insufficient developer quantity. On bigger features it is possible to see the progress of development. Allow a little over-development, once resist has cleared.
2. These results are based on using a bare Silicon substrate. Films present on substrates and/or other types of substrates may affect the exposure and/or development time. Adjust as needed.